

*B-1 cont*

said first electrode layer including at least one selected from a first metal group consisting

of Ti, Hf, Zr, Nb, Ta and Sc,

said second electrode layer including at least one selected from a second metal group  
consisting of Ni, Pd and Co, and

*Ni / Au*

said third electrode layer including Au.

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8. (Amended) An electrode structure on a p-type III group nitride semiconductor  
layer, comprising first, second and third electrode layers successively stacked on said  
semiconductor layer,

*N*  
*Sub C'*

said first electrode layer including at least one selected from a first metal group consisting  
of Ti, Hf, Zr, Nb, Ta and Sc,

said second electrode layer including at least one selected from a second metal group  
consisting of Ni and Co, and

said third electrode layer including Au.

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Please add new claims 12-14 as follows:

*Sub D'*  
*B-3*

12. The electrode structure according to claim 8, wherein said first electrode layer  
includes a nitride of a metal included in said first metal group, and also includes a compound of  
Ga and a metal included in said second metal group.

13. An electrode structure on a p-type III group nitride semiconductor layer,  
comprising first, second and third electrode layers successively stacked on said semiconductor  
layer,

*3*  
*1*  
*2*  
*com*

said first electrode layer having a thickness of 10 to 500 nm and including at least one selected from a first metal group consisting of Ti, Hf, Zr, Nb, Ta and Sc,  
said second electrode layer having a thickness of 50 nm or more and including at least one selected from a second metal group consisting of Ni, Pd and Co, and  
said third electrode layer having a thickness of 50 nm or more and including Au.

14. The electrode structure according to claim 13, wherein said first electrode layer includes a nitride of a metal included in said first metal group, and also includes a compound of Ga and a metal included in said second metal group.

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